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November 2013

# FDP12N50 / FDPF12N50T N-Channel UniFET<sup>TM</sup> MOSFET 500 V, 11.5 A, 650 m $\Omega$

#### **Features**

- $R_{DS(on)}$  = 550 m $\Omega$  (Typ.) @  $V_{GS}$  = 10 V,  $I_D$  = 6 A
- Low Gate Charge (Typ. 22 nC)
- Low C<sub>rss</sub> (Typ. 11 pF)
- · 100% Avalanche Tested
- · RoHS Compliant

## **Applications**

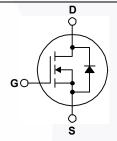
- LCD/LED/PDP TV
- · Lighting
- · Uninterruptible Power Supply

## Description

UniFET<sup>TM</sup> MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.







## **MOSFET Maximum Ratings** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol		Parameter		FDP12N50	FDPF12N50T	Unit	
$V_{DSS}$	Drain to Source Voltage	Drain to Source Voltage			500		
$V_{GSS}$	Gate to Source Voltage			±	:30	V	
	Drain Current	- Continuous (T <sub>C</sub> = 25°C	5)	11.5	11.5 *	Α	
ID	Diamourient	- Continuous (T <sub>C</sub> = 100°	C)	6.9	6.9 *	A	
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	46	46 *	Α	
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)			456		mJ	
I <sub>AR</sub>	Avalanche Current		(Note 1)	1	1.5	Α	
E <sub>AR</sub>	Repetitive Avalanche Er	nergy	(Note 1)	1) 16.7		mJ	
dv/dt	Peak Diode Recovery d	v/dt	(Note 3)	4	1.5	V/ns	
Б	Dower Dissinction	(T <sub>C</sub> = 25°C)		165	42	W	
$P_{D}$	Power Dissipation	- Derate Above 25°C		1.33	0.3	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150		οС	
TL	Maximum Lead Temper	ature for Soldering, 1/8" from Case	for 5 Seconds	3	00	οС	

<sup>\*</sup>Drain current limited by maximum junction temperature

#### **Thermal Characteristics**

Symbol	Parameter	FDP12N50	FDPF12N50T	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.75	3.0	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	62.5	*C/VV

## **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDP12N50	FDP12N50	TO-220	Tube	N/A	N/A	50 units
FDPF12N50T	FDPF12N50T	TO-220F	Tube	N/A	N/A	50 units

## **Electrical Characteristics** T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_J = 25^{\circ} C$	500	-	-	V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, Referenced to 25°C	-	0.5	-	V/°C
1	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V	-	-	1	μA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 400 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	-	10	μΑ
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>GS</sub> = ±30 V, V <sub>DS</sub> = 0 V	-	-	±100	nA

#### **On Characteristics**

V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$	3.0	-	5.0	V
R <sub>DS(on)</sub>	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 6 \text{ A}$	-	0.55	0.65	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 40 V, I <sub>D</sub> = 6 A	ı	11.5	ı	S

## **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V - 25 V V - 2 V		-	985	1315	pF
C <sub>oss</sub>	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1  MHz		-\	140	190	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 1 101112	-	- \	11	17	pF
$Q_g$	Total Gate Charge at 10V	V <sub>DS</sub> = 400 V, I <sub>D</sub> = 11.5 A,		- \	22	30	nC
$Q_{gs}$	Gate to Source Gate Charge	V <sub>GS</sub> = 10 V	-	-	6	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge	(N	lote 4)	-	9	-	nC

## **Switching Characteristics**

t <sub>d(on)</sub>	Turn-On Delay Time		-	24	60	ns
t <sub>r</sub>		$V_{DD} = 250 \text{ V}, I_D = 11.5 \text{ A},$	-	50	110	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS}$ = 10 V, $R_G$ = 25 $\Omega$	-	45	100	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)	- /	30	70	ns

#### **Drain-Source Diode Characteristics**

ls	Maximum Continuous Drain to Source Diod	Maximum Continuous Drain to Source Diode Forward Current		-	11.5	Α
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	46	Α
$V_{SD}$	Drain to Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 11.5 A	-	-	1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 11.5 A,	-	375	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	$dI_F/dt = 100 A/\mu s$	-	3.5	-	μС

#### Notes

- ${\it 1. Repetitive\ rating: pulse-width\ limited\ by\ maximum\ junction\ temperature.}$
- 2. L = 6.9 mH,  $I_{AS}$  = 11.5 A,  $V_{DD}$  = 50 V,  $R_{G}$  = 25  $\Omega$ , starting  $T_{J}$  = 25°C.
- 3.  $I_{SD} \le 11.5$  A, di/dt  $\le 200$  A/ $\mu$ s,  $V_{DD} \le BV_{DSS}$ , starting  $T_J$  = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

## **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

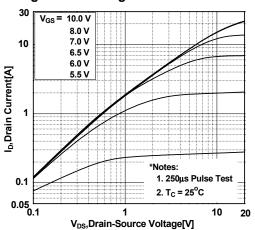


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

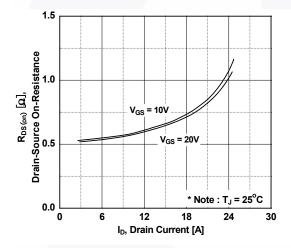


Figure 5. Capacitance Characteristics

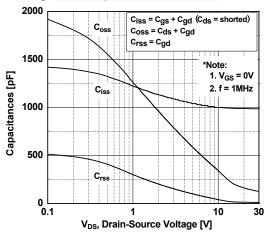


Figure 2. Transfer Characteristics

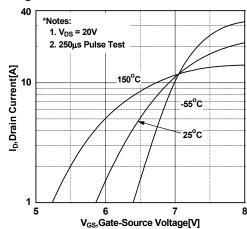


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

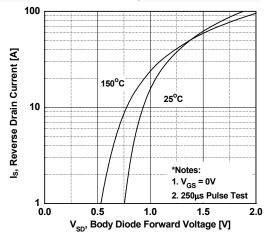
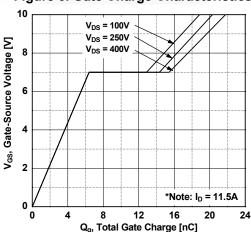


Figure 6. Gate Charge Characteristics



## **Typical Performance Characteristics** (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

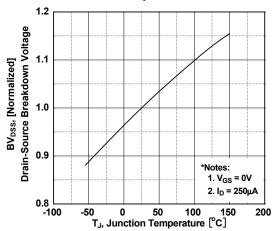


Figure 9-1. Maximum Safe Operating Area - FDP12N50

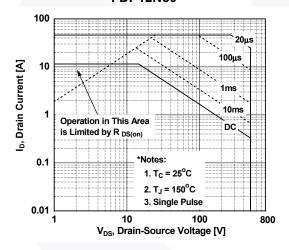


Figure 8. On-Resistance Variation vs. Temperature

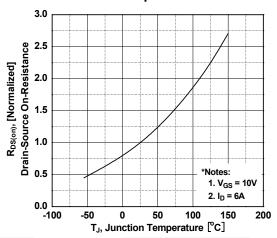


Figure 9-2. Maximum Safe Operating Area - FDPF12N50T

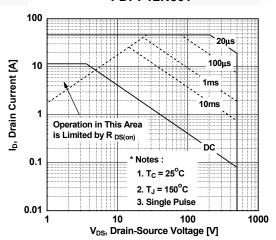
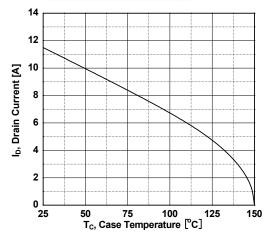


Figure 10. Maximum Drain Current vs. Case Temperature



## **Typical Performance Characteristics** (Continued)

Figure 11-1. Transient Thermal Response Curve - FDP12N50

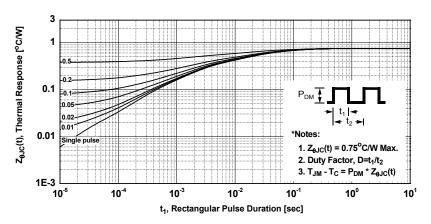
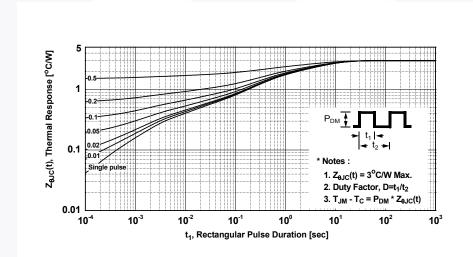


Figure 11-2. Transient Thermal Response Curve - FDPF12N50T



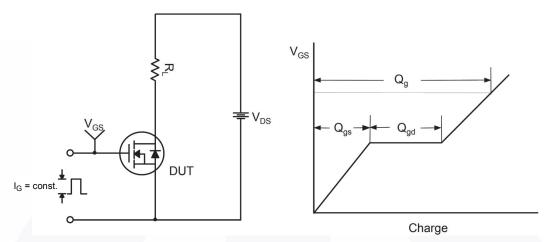


Figure 12. Gate Charge Test Circuit & Waveform

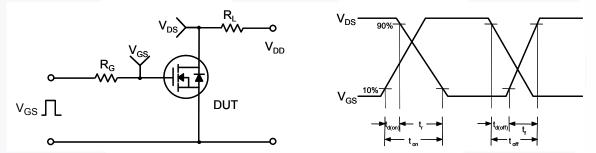


Figure 13. Resistive Switching Test Circuit & Waveforms

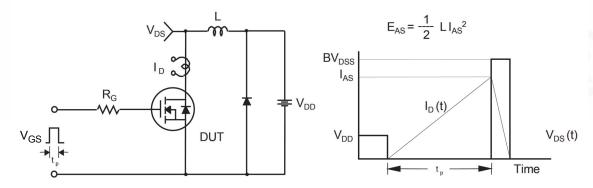


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

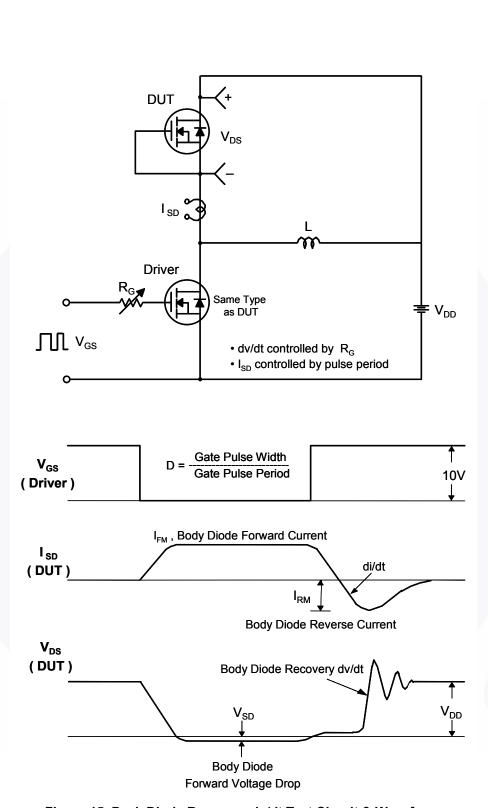


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

#### **Mechanical Dimensions**

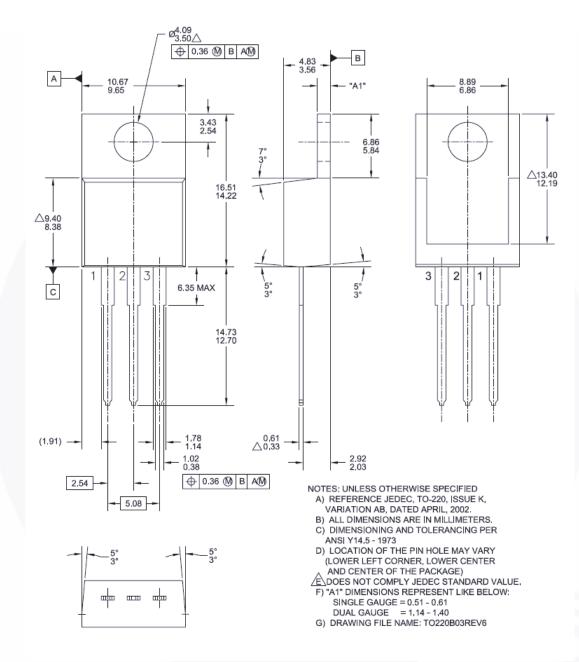


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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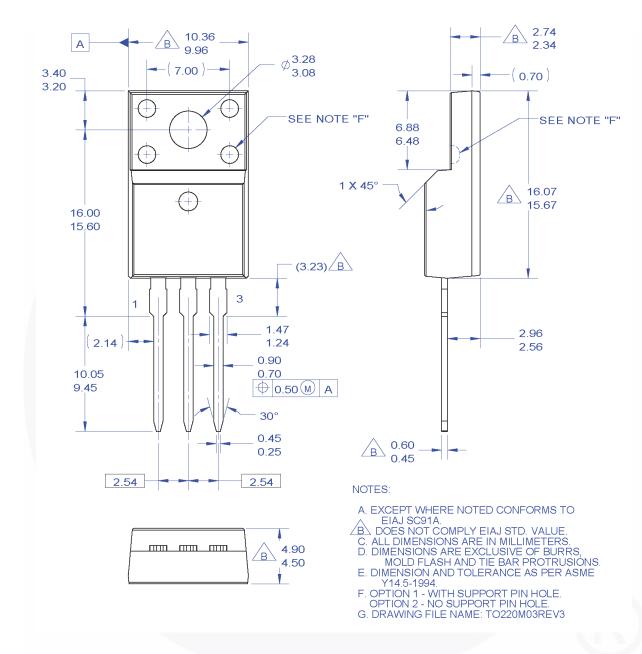


Figure 17. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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